

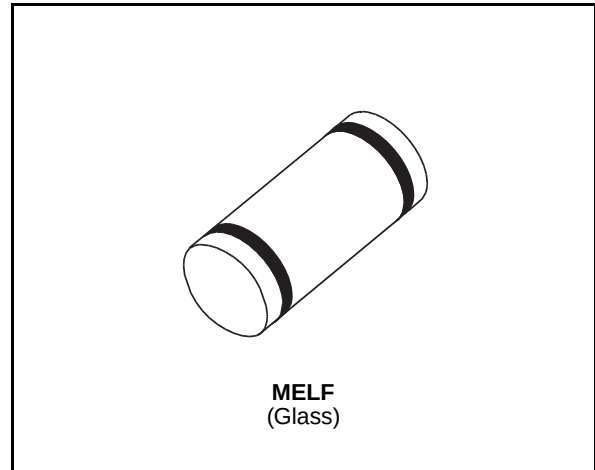


TMBYV 10-40

SMALL SIGNAL SCHOTTKY DIODES

DESCRIPTION

Metal to silicon rectifier diodes in glass case featuring very low forward voltage drop and fast recovery time, intended for low voltage switching mode power supply, polarity protection and high frequency circuits.



ABSOLUTE MAXIMUM RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		40	V
$I_F (AV)$	Average Forward Current	$T_i = 60\text{ }^{\circ}\text{C}$	1	A
I_{FSM}	Surge non Repetitive Forward Current	$T_i = 25\text{ }^{\circ}\text{C}$ $t_p = 10\text{ms}$	25 Sinusoidal Pulse	A
		$T_i = 25\text{ }^{\circ}\text{C}$ $t_p = 300\mu\text{s}$	50 Rectangular Pulse	
T_{stg} T_j	Storage and Junction Temperature Range		- 65 to 150 - 65 to 125	$^{\circ}\text{C}$ $^{\circ}\text{C}$
T_L	Maximum Lead Temperature for Soldering during 15s		260	$^{\circ}\text{C}$

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-l)}$	Junction-leads	110	$^{\circ}\text{C/W}$

* Pulse test: $t_p \leq 300\mu\text{s}$ $\delta < 2\%$.

ELECTRICAL CHARACTERISTICS
STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I_R^*	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			0.5	mA
	$T_j = 100^\circ\text{C}$				10	
V_F^*	$I_F = 1\text{A}$	$T_j = 25^\circ\text{C}$			0.55	V
	$I_F = 3\text{A}$				0.85	

** Pulse test: $t_p \leq 300\mu\text{s}$ $\delta < 2\%$.

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
C	$T_j = 25^\circ\text{C}$	$V_R = 0$		220		pF

Forward current flow in a Schottky rectifier is due to majority carrier conduction. So reverse recovery is not affected by storage charge as in conventional PN junction diodes.

Nevertheless, when the device switches from forward biased condition to reverse blocking state, current is required to charge the depletion capacitance of the diode.

This current depends only of diode capacitance and external circuit impedance. Satisfactory circuit behaviour analysis may be performed assuming that Schottky rectifier consists of an ideal diode in parallel with a variable capacitance equal to the junction capacitance (see fig. 5 page 4/4).

Fig. 1 : Forward current versus forward voltage at low level (typical values).

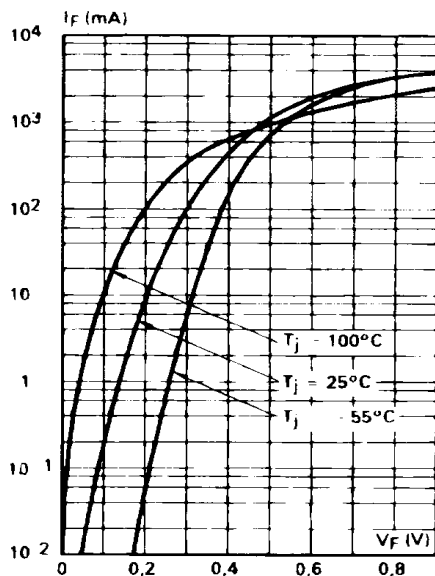


Fig. 2 : Forward current versus forward voltage at high level (typical values).

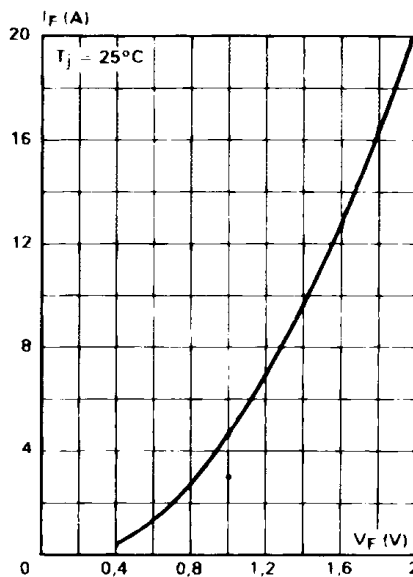


Fig. 3 : Reverse current versus junction temperature.

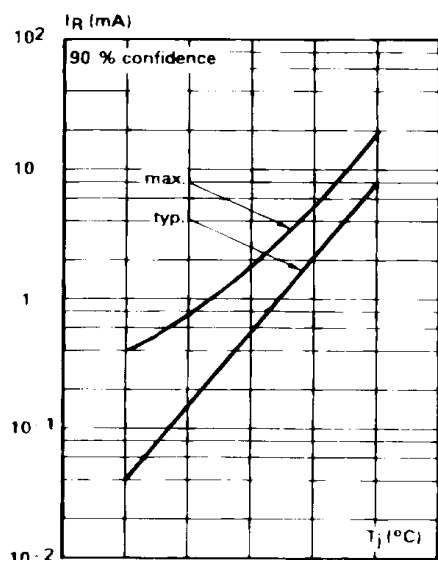


Fig. 4 : Reverse current versus VRRM in per cent.

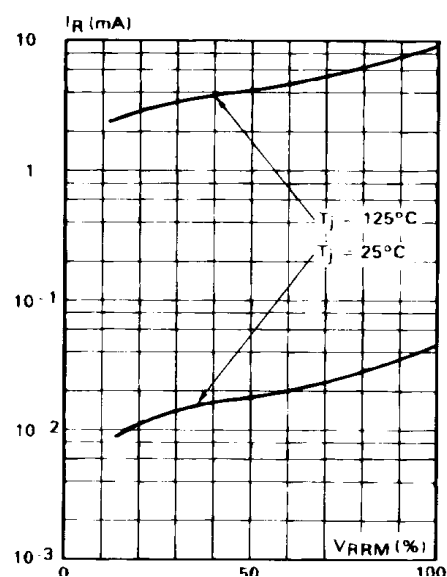


Fig. 5 : Capacitance C versus reverse applied voltage V_R (typical values)

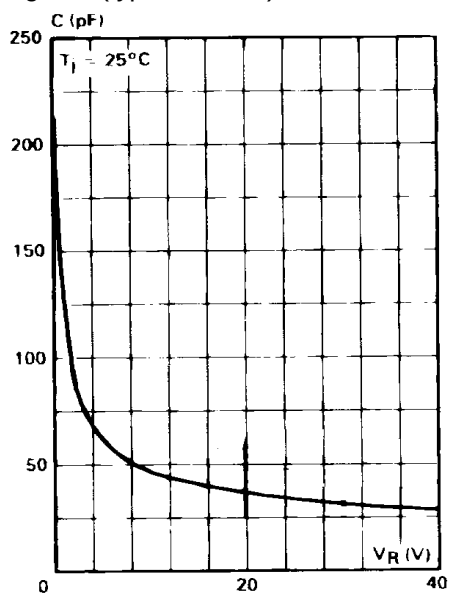
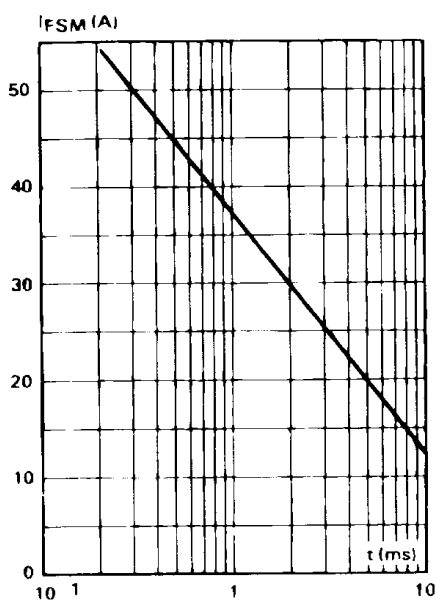
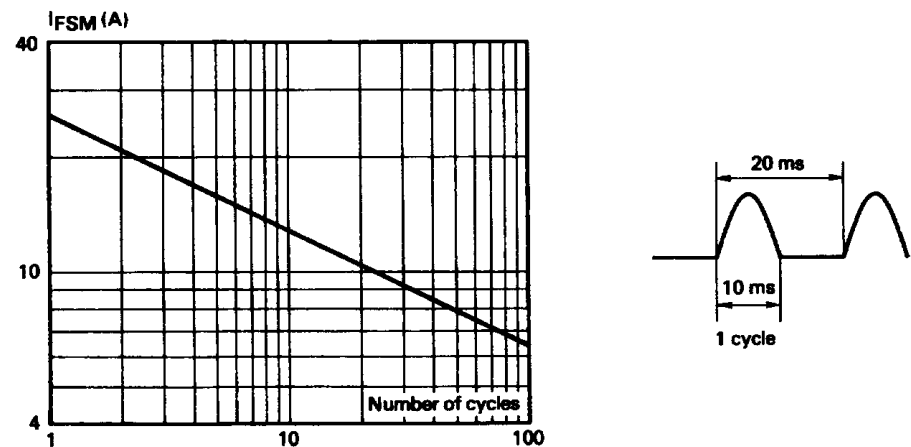


Fig. 6 : Surge non repetitive forward current for a rectangular pulse with $t \hat{=} 10$ ms.

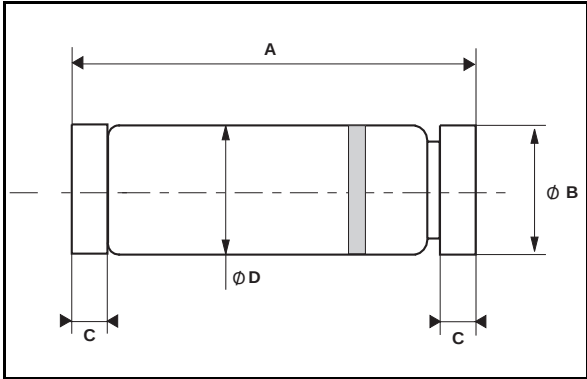


TMBYV10-40

Fig. 7 : Surge non repetitive forward current versus number of cycles.



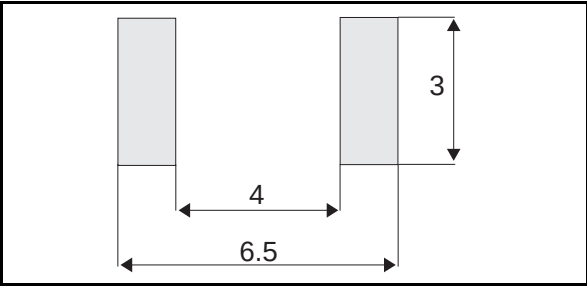
PACKAGE MECHANICAL DATA
MELF Glass



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.80		5.20	0.189		0.205
Ø B	2.50		2.65	0.098		0.104
C	0.45		0.60	0.018		0.024
Ø D		2.50			0.098	

Cooling method: by convection and conduction
Marking: ring at cathode end.
Weight: 0.139g

FOOT PRINT DIMENSIONS (Millimeter)



ORDERING CODE : TMBYV10-40 FILM

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics
© 1998 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - France - Germany - Italy - Japan - Korea - Malaysia - Malta - Mexico - Morocco -
The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.

